

OPA6616

Super Bright

Red LED Chip

GaAlAs / GaAs

1. Material Substrate GaAs (P Type)
Epitaxial Layer GaAlAs (N/P Type)

2. Electrode N (Cathode) Side Gold Alloy
P (Anode) Side Gold Alloy

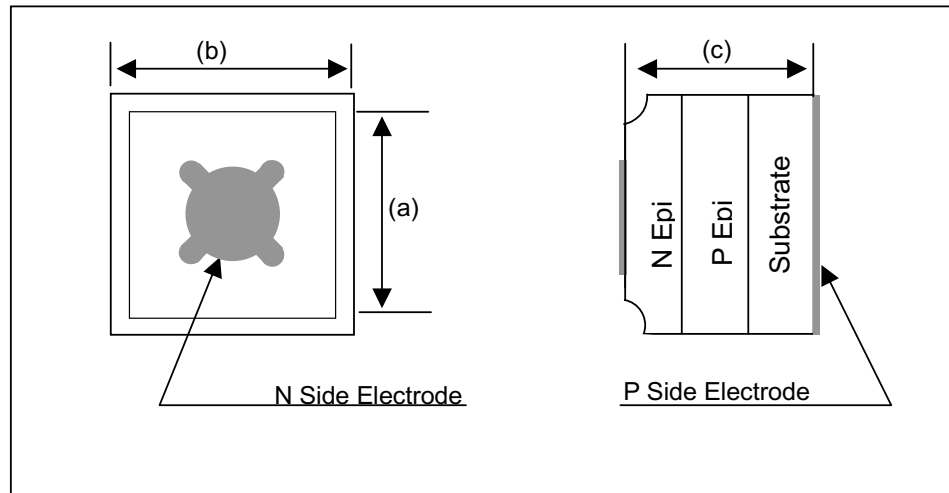
3. Electro-Optical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Forward Voltage	$V_{F(1)}$		1.6		V	$I_F=1\text{mA}$
	$V_{F(2)}$		1.9	2.3	V	$I_F=20\text{mA}$
Reverse Voltage	V_R	5.0			V	$I_R=10\mu\text{A}$
Brightness	I_V	450	700		mcd	$I_F=20\text{mA}$
Wavelength	Hue		645		nm	$I_F=20\text{mA}$
	$\Delta\lambda$		20		nm	$I_F=20\text{mA}$

※ Note: Assembled into T1³/₄ plastic package.

4. Mechanical Data

- (a) Emission Area ----- 9mil × 9mil
- (b) Bottom Area ----- 11mil × 11mil
- (c) Chip Thickness ----- 11mil



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